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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

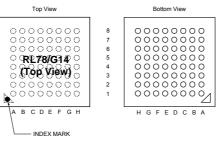
XFI

2000	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5К х 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104gadfb-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

• 64-pin plastic FLGA (5 × 5 mm, 0.5 mm pitch)



	А	В	С	D	E	F	G	н	
8	EVDD0	EVsso	P121/X1	P122/X2/ EXCLK	P137/INTP0	P123/XT1	P124/XT2/ EXCLKS	P120/ANI19/ VCOUT0 Note 1	8
7	P60/SCLA0	Vdd	Vss	REGC	RESET	P01/TO00/ TRGCLKB/ TRJIO0	P00/TI00/ TRGCLKA/ (TRJO0)	P140/ PCLBUZ0/ INTP6	7
6	P61/SDAA0	P62/SSI00	P63	P40/TOOL0	P41/(TRJIO0)	P43/(INTP9)	P02/ANI17/ SO10/TxD1	P141/ PCLBUZ1/ INTP7	6
5	P77/KR7/ INTP11/(TXD2)	P31/TI03/ TO03/INTP4/ (PCLBUZ0)/ (TRJIO0)	P53/(INTP2)	P42/(INTP8)	P03/ANI16/ SI10/RxD1/ SDA10	P04/SCK10/ SCL10	P130	P20/ANI0/ AVrefp	5
4	P75/KR5/ INTP9/ SCK01/ SCL01	P76/KR6/ INTP10/ (RXD2)	P52/(INTP1)	P54/(INTP3)	P16/TI01/ TO01/INTP5/ TRDIOC0/ IVREF0 Note 1/ (SI00)/(RXD0)	P21/ANI1/ AVrefm	P22/ANI2/ ANO0 Note 1	P23/ANI3/ ANO1 ^{Note 1}	4
3	P70/KR0/ SCK21/ SCL21	P73/KR3/ SO01	P74/KR4/ INTP8/SI01/ SDA01	P17/TI02/TO02/ TRDIOA0/ TRDCLK/ IVCMP0 Note 1/ (SO00)/(TXD0)	P15/SCK20/ SCL20/ TRDIOB0/ (SDAA0)	P12/SO11/ TRDIOB1/ IVREF1 Note 1/ (INTP5)/ (TxD0_1) Note 2	P24/ANI4	P26/ANI6	3
2	P30/INTP3/ RTC1HZ/ SCK00/ SCL00/TRJO0	P72/KR2/ SO21	P71/KR1/ SI21/SDA21	P06/(INTP11)/ (TRJIO0)	P14/RxD2/ SI20/SDA20/ TRDIOD0/ (SCLA0)	P11/SI11/ SDA11/ TRDIOC1/ (RxD0_1) Note 2	P25/ANI5	P27/ANI7	2
1	P05/(INTP10)	P50/INTP1/ SI00/RxD0/ TOOLRxD/ SDA00/ TRGIOA/ (TRJO0)	P51/INTP2/ SO00/TxD0/ TOOLTxD/ TRGIOB	P55/ (PCLBUZ1)/ (SCK00)/ (INTP4)	P13/TxD2/ SO20/ TRDIOA1/ IVCMP1 Note 1	P10/SCK11/ SCL11/ TRDIOD1	P146	P147/ANI18/ VCOUT1 Note 1	1
	А	В	С	D	E	F	G	Н	

Note 1. Mounted on the 96 KB or more code flash memory products.

Note 2. Mounted on the 384 KB or more code flash memory products.

Caution 1. Make EVsso pin the same potential as VSS pin.

Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.

Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$

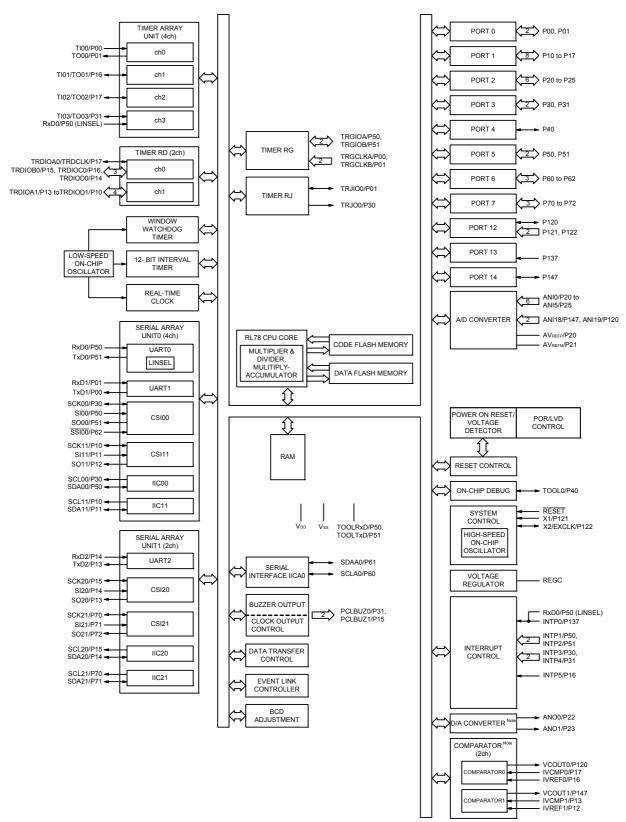
Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.

Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

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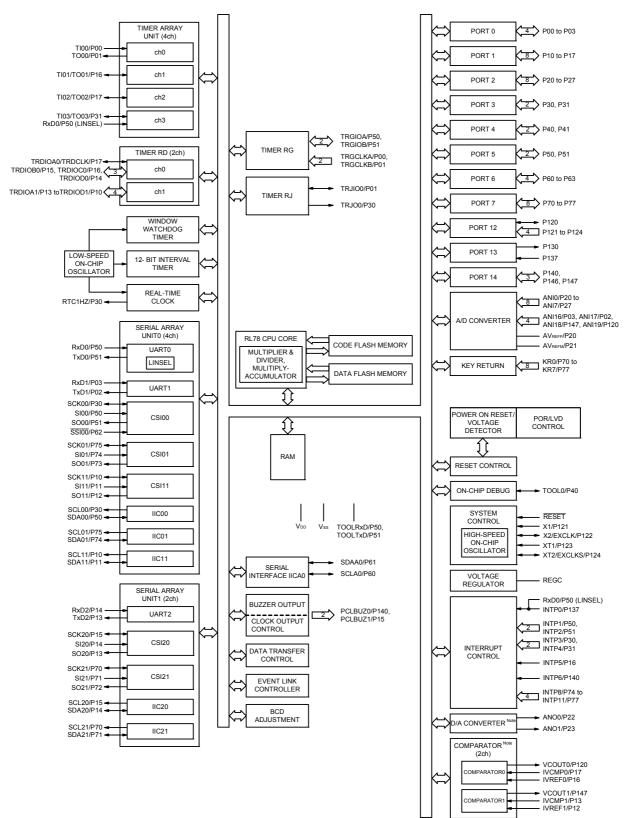
1.5.3 36-pin products



Note Mounted on the 96 KB or more code flash memory products.



1.5.7 52-pin products



Note Mounted on the 96 KB or more code flash memory products.



Items	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Output voltage, high	VOH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57,	4.0 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -10.0 mA	EVDD0 - 1.5			V
		P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
		P111, P120, P130, P140 to P147	1.8 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -1.5 mA	EVDD0 - 0.5			V
			1.6 V ≤ EVDD0 < 1.8 V, Іон1 = -1.0 mA	EVDD0 - 0.5			V
	Voh2	P20 to P27, P150 to P156	1.6 V ≤ VDD ≤ 5.5 V, IOH2 = -100 μA	Vdd - 0.5			V
Output voltage, low		P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 20.0 mA			1.3	V
			$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 8.5 \text{ mA}$			0.7	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 3.0 mA			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 0.6 mA			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 0.3 mA			0.4	V
	Vol2	P20 to P27, P150 to P156	$1.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V},$ $I_{OL2} = 400 \mu\text{A}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 15.0 mA			2.0	V
			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 5.0 mA			0.4	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 3.0 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 2.0 mA			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 1.0 mA			0.4	V

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(4/5)

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$ @1 MHz to 32 MHz
	2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode:	1.8 V \leq VDD \leq 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode:	1.6 V \leq VDD \leq 5.5 V@1 MHz to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.) Remark 3. file:
- High-speed on-chip oscillator clock frequency (32 MHz max.) Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

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- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 4.** When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 32 MHz
 - 2.4 V \leq VDD \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 8 MHz
 - LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ @1 MHz to 4 MHz
- Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- **Remark 3.** file: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsuB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C



Parameter	Parameter Symbol Conditions		ditions	HS (high-spee mode	HS (high-speed main) mode		d main)	LV (low-voltag mode	e main)	Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle	t КСҮ2	$4.0~V \leq EV_{DD0} \leq 5.5~V$	20 MHz < fмск	8/fмск		_		—		ns	
time Note 5			fмск ≤ 20 MHz	6/fмск		6/fмск		6/fмск		ns	
		$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	16 MHz < fмск	8/fмск		_		—		ns	
			fмск ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns	
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns	
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns	
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns	
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		_		6/fмск and 1500		6/fмск and 1500		ns	
SCKp high-/	tкн2,	$4.0~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксү2/2 - 7		tксү2/2 - 7		tксү2/2 - 7		ns	
low-level width	tĸ∟2	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		tксү2/2 - 8		tkcy2/2 - 8		tkcy2/2 - 8		ns	
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү2/2 - 18		tксү2/2 - 18		tксү2/2 - 18		ns	
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		tксү2/2 - 66		tkcy2/2 - 66		tксү2/2 - 66		ns	
1.6 V ≤ EV		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		—		tkcy2/2 - 66		tксү2/2 - 66		ns	
SIp setup time	tsik2	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1/fмск + 20		1/fмск + 30		1/fмск + 30		ns	
(to SCKp↑) Note 1		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns	
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1/fмск + 40		1/fмск + 40		1/fмск + 40		ns	
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		—		1/fмск + 40		1/fмск + 40		ns	
SIp hold time	tksi2	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns	
(from SCKp↑) Note 2		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		1/fмск + 250		1/fмск + 250		1/fмск + 250		ns	
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		—		1/fмск + 250		1/fмск + 250		ns	
Delay time from SCKp↓ to	tkso2	C = 30 pF Note 4	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		2/fмск + 44		2/fмск + 110		2/fмск + 110	ns	
SOp output Note 3				$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		2/fмск + 75		2/fмск + 110		2/fмск + 110	ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		2/fмск + 100		2/fмск + 110		2/fмск + 110	ns	
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		2/fмск + 220		2/fмск + 220		2/fмск + 220	ns	
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		—		2/fмск + 220		2/fмск + 220	ns	

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

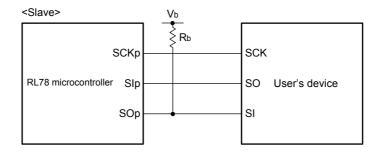
Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EVDD0 \ge Vb$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VoD tolerance (for the 30- to 52-pin products)/EVoD tolerance (for the 64- to 100-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
- Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
 Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.



Parameter	Symbol	Conditions		speed main) node		speed main) 10de		oltage main) 10de	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	1
SCLr clock frequency	fsc∟	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		1000 Note 1		300 Note 1		300 Note 1	kHz
				400 Note 1		300 Note 1		300 Note 1	kHz
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		400 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:VD} \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2}, \\ C_b = 100 \ \text{pF}, \ R_b = 5.5 \ \text{k}\Omega \end{array}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t∟ow		475		1550		1550		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	475		1550		1550		ns
			1150		1550		1550		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1150		1550		1550		ns
		$ \begin{split} & 1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V \; \mbox{Note 2}, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split} $	1550		1550		1550		ns
Hold time when SCLr = "H"	tнıgн	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	245		610		610		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	200		610		610		ns
			675		610		610		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	600		610		610		ns
		$\label{eq:VD0} \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note} \ 2, \\ C_b = 100 \ \text{pF}, \ R_b = 5.5 \ \text{k}\Omega \end{array}$	610		610		610		ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified l²C mode) (TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

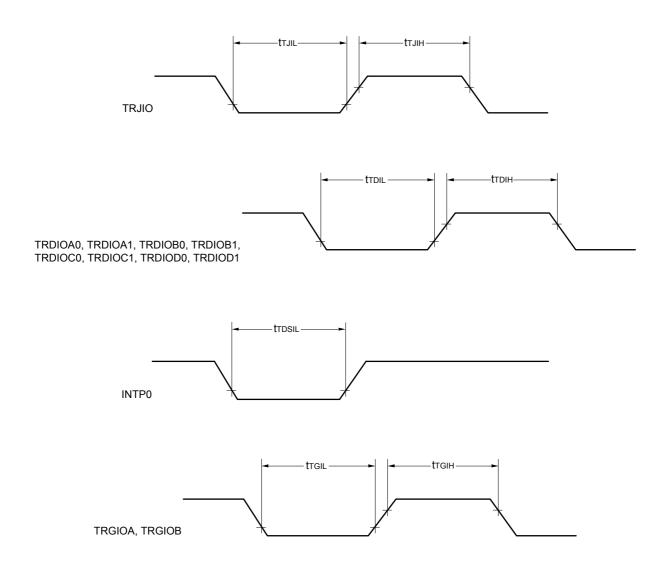


$(1A = -40 \text{ to } +105 \text{ C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VD1} \le 3.5 \text{ V}, \text{VSS} = \text{EVSS0} = \text{EVSS1} = 0 \text{ V})$							(2/2)
Items	Symbol	Conditions			TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tтdін, tтdі∟	TRDIOA0, TRDIOA1, TRDIOI TRDIOC0, TRDIOC1, TRDIO	, ,	3/fclк			ns
Timer RD forced cutoff signal	t TDSIL	P130/INTP0	$2MHz < f_{CLK} \le 32 MHz$	1			μs
input low-level width			fclk ≤ 2 MHz	1/fclк + 1			
Timer RG input high-level width, low-level width	tтGін, tтGі∟	TRGIOA, TRGIOB		2.5/fclk			ns
TO00 to TO03,	fтo	HS (high-speed main) mode	$4.0 \text{ V} \leq EV_{DD0} \leq 5.5 \text{ V}$			16	MHz
TO10 to TO13,			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			8	MHz
TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency			2.4 V ≤ EVDD0 < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-speed main) mode	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$			16	MHz
frequency			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 4.0 \text{ V}$			8	MHz
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			4	MHz
Interrupt input high-level	tinth,	INTP0	$2.4~V \leq V \text{DD} \leq 5.5~V$	1			μs
width, low-level width	tintl	INTP1 to INTP11	$2.4~V \leq EV_{DD0} \leq 5.5~V$	1			μs
Key interrupt input low-level width	tкr	KR0 to KR7	$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	250			ns
RESET low-level width	trsl			10			μs

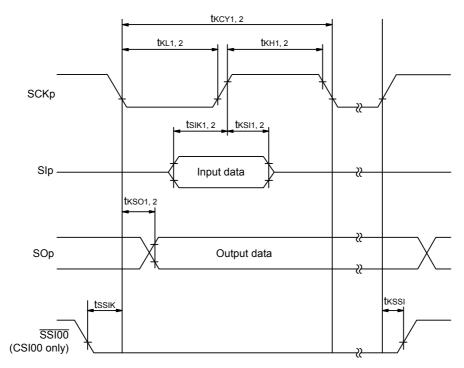
(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)



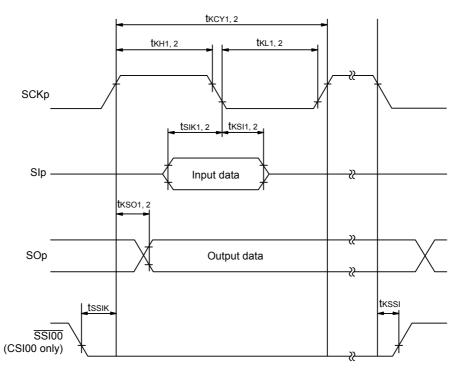






CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31) Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions	HS (high-spe	Unit	
			MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note}	tsiкı		88		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	88		ns
		$\label{eq:2.4} \begin{split} & 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	220		ns
SIp hold time (from SCKp↓) ^{Note}	tksi1		38		ns
		$\begin{split} & 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ & 2.3 \ V \leq V_b \leq 2.7 \ V, \\ & C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	38		ns
		$\label{eq:VDD0} \begin{split} & 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1			50	ns
		$\begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		50	ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		50	ns

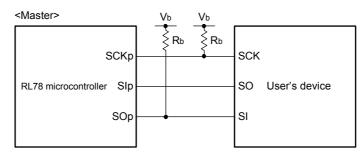
Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Remarks are listed on the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

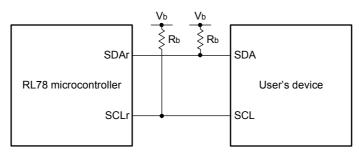
CSI mode connection diagram (during communication at different potential



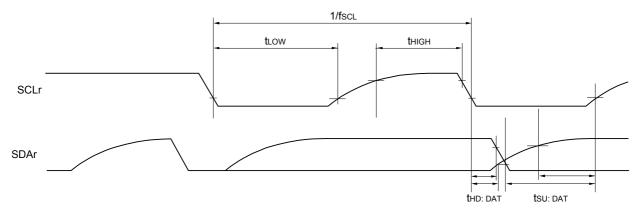
- **Remark 5.** Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 6.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 7. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
- Remark 8. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)

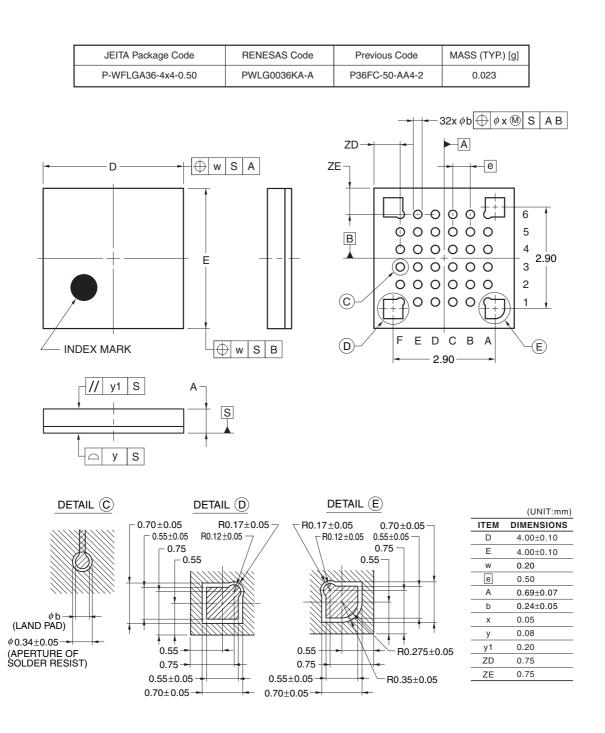


- **Remark 1.** Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 30, 31), g: PIM, POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fMCK: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 01, 02, 10, 12, 13)



4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA



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R5F104GAANA, R5F104GCANA, R5F104GDANA, R5F104GEANA, R5F104GFANA, R5F104GGANA, R5F104GHANA, R5F104GJANA

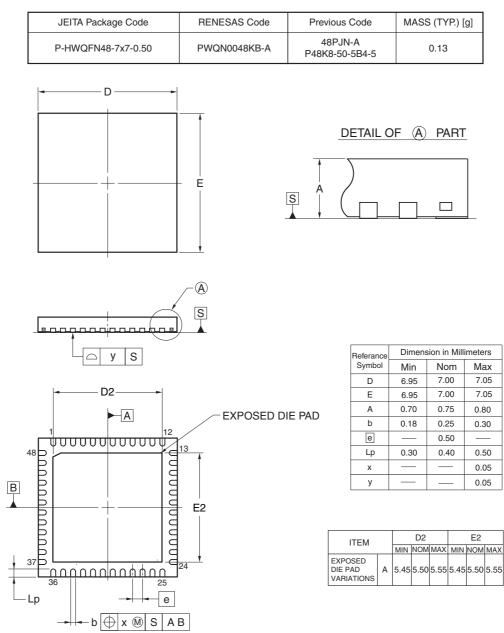
R5F104GADNA, R5F104GCDNA, R5F104GDDNA, R5F104GEDNA, R5F104GFDNA, R5F104GGDNA, R5F104GJDNA, R5F104GJDNA

R5F104GAGNA, R5F104GCGNA, R5F104GDGNA, R5F104GEGNA, R5F104GFGNA, R5F104GGGNA,

R5F104GHGNA, R5F104GJGNA

R5F104GKANA, R5F104GLANA

R5F104GKGNA, R5F104GLGNA

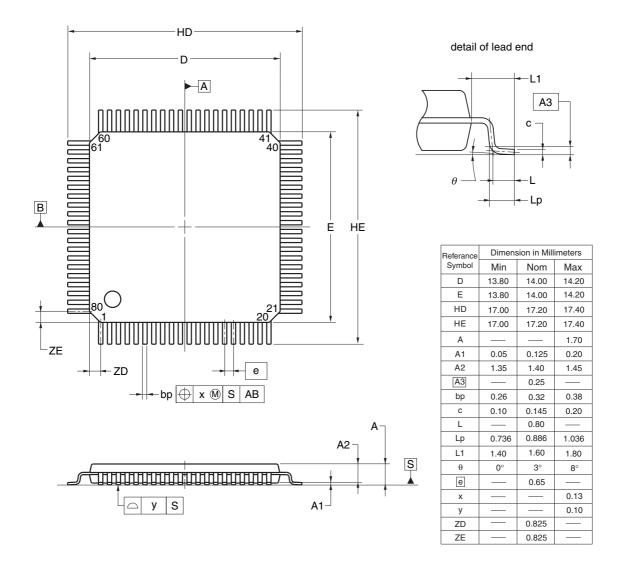


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R5F104MFAFA, R5F104MGAFA, R5F104MHAFA, R5F104MJAFA R5F104MFDFA, R5F104MGDFA, R5F104MHDFA, R5F104MJDFA R5F104MFGFA, R5F104MGGFA, R5F104MHGFA, R5F104MJGFA R5F104MKAFA, R5F104MLAFA R5F104MKGFA, R5F104MLGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



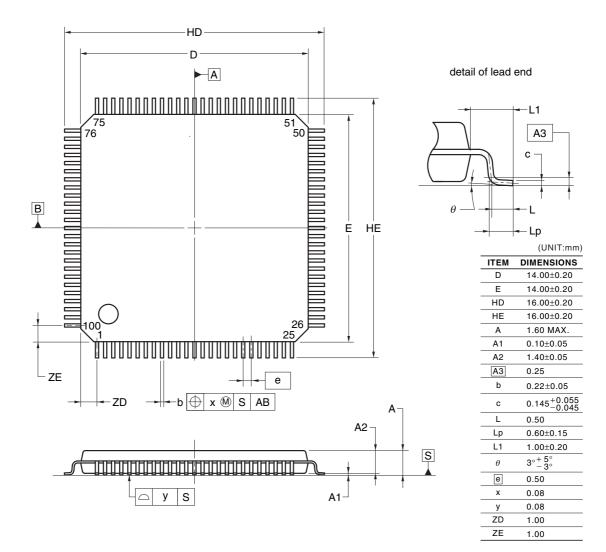
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4.10 100-pin products

R5F104PFAFB, R5F104PGAFB, R5F104PHAFB, R5F104PJAFB R5F104PFDFB, R5F104PGDFB, R5F104PHDFB, R5F104PJDFB R5F104PFGFB, R5F104PGGFB, R5F104PHGFB, R5F104PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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REVISION HISTORY

RL78/G14 Datasheet

Devi	Dete		Description
Rev.	Date	Page	Summary
2.00	Oct 25, 2013	112 to 169	Addition of CHAPTER 3 ELECTRICAL SPECIFICATIONS
		171 to 187	Modification of 4.1 30-pin products to 4.10 100-pin products
3.00	Feb 07, 2014	All	Addition of products with maximum 512 KB flash ROM and 48 KB RAM
		1	Modification of 1.1 Features
		2	Modification of ROM, RAM capacities and addition of note 3
		3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14
		6 to 8	Addition of part number
		15, 16	Modification of 1.3.6 48-pin products
		17	Modification of 1.3.7 52-pin products
		18, 19	Modification of 1.3.8 64-pin products
		20	Modification of 1.3.9 80-pin products
		21, 22	Modification of 1.3.10 100-pin products
		35, 37, 39, 41, 43, 45, 47	Modification of operating ambient temperature in 1.6 Outline of Functions
		42, 43	Addition of table of 48-pin, 52-pin, 64-pin products (code flash memory 384 KB to 512 KB)
		46, 47	Addition of table of 80-pin, 100-pin products (code flash memory 384 KB to 512 KB)
		65 to 68	Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products
		118	Modification of 2.7 Data Memory Retention Characteristics
		137 to 140	Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products
		180	Modification of 3.7 Data Memory Retention Characteristics
		189, 190	Addition and modification of 4.6 48-pin products
		191	Modification of 4.7 52-pin products
		193 to 195	Addition and modification of 4.8 64-pin products
		198, 199	Addition and modification of 4.9 80-pin products
		201, 202	Addition and modification of 4.10 100-pin products
3.20	Jan 05, 2015	p.2	Deletion of R5F104JK and R5F104JL from the list of ROM and RAM capacities and modification of note
		p.6	Deletion of ordering part numbers of R5F104JK and R5F104JL from 52-pin plastic LQFP package in 1.2 Ordering Information
		p.6 to 8	Deletion of note 2 in 1.2 Ordering Information
		p.17	Deletion of note 2 in 1.3.7 52-pin products
		p.36, 39, 42, 45, 48, 50, 52	Modification of description in 1.6 Outline of Functions
		p.46, 48	Deletion of description of 52-pin in 1.6 Outline of Functions
		p.47	Modification of note of 1.6 Outline of Functions
		p.62, 64, 66, 68, 70, 72	Modification of specifications in 2.3.2 Supply current characteristics